

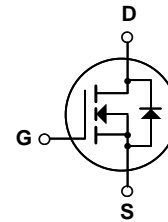
**Features**

- 55A, 100V,  $R_{DS(on)} = 0.026\Omega$  @  $V_{GS} = 10\text{ V}$
- Low gate charge ( typical 75 nC)
- Low  $C_{rss}$  ( typical 130 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- 175°C maximum junction temperature rating

**General Description**

These N-Channel enhancement mode power field effect transistors are produced using Kersemi proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for low voltage applications such as audio amplifier, high efficiency switching DC/DC converters, and DC motor control.

**TO-220**

**Absolute Maximum Ratings**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	KSM55N10	Units
$V_{DSS}$	Drain-Source Voltage	100	V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ ) - Continuous ( $T_C = 100^\circ\text{C}$ )	55	A
		38.9	A
$I_{DM}$	Drain Current - Pulsed (Note 1)	220	A
$V_{GSS}$	Gate-Source Voltage	$\pm 25$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	1100	mJ
$I_{AR}$	Avalanche Current (Note 1)	55	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	15.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	6.0	V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ ) - Derate above $25^\circ\text{C}$	155	W
		1.03	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

**Thermal Characteristics**

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.97	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.5	--	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ\text{C}/\text{W}$

**Electrical Characteristics**
 $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	100	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	0.1	--	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	$\mu\text{A}$
		$V_{DS} = 80\text{ V}, T_C = 150^\circ\text{C}$	--	--	10	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 25\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -25\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

**On Characteristics**

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 27.5\text{ A}$	--	0.021	0.026	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 27.5\text{ A}$ (Note 4)	--	38	--	S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	2100	2730	pF
$C_{oss}$	Output Capacitance		--	640	830	pF
$C_{riss}$	Reverse Transfer Capacitance		--	130	170	pF

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50\text{ V}, I_D = 55\text{ A},$ $R_G = 25\ \Omega$	--	25	60	ns
$t_r$	Turn-On Rise Time		--	250	510	ns
$t_{d(off)}$	Turn-Off Delay Time		--	110	230	ns
$t_f$	Turn-Off Fall Time		(Note 4, 5)	--	140	290
$Q_g$	Total Gate Charge	$V_{DS} = 80\text{ V}, I_D = 55\text{ A},$ $V_{GS} = 10\text{ V}$	--	75	98	nC
$Q_{gs}$	Gate-Source Charge		--	13	--	nC
$Q_{gd}$	Gate-Drain Charge		(Note 4, 5)	--	36	--

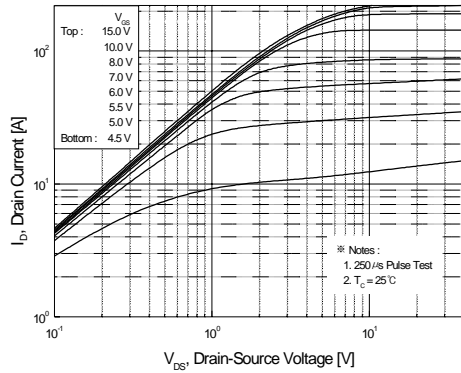
**Drain-Source Diode Characteristics and Maximum Ratings**

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	55	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	220	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 55\text{ A}$	--	--	1.5	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 55\text{ A},$	--	100	--	ns
$Q_{rr}$	Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	380	--	nC

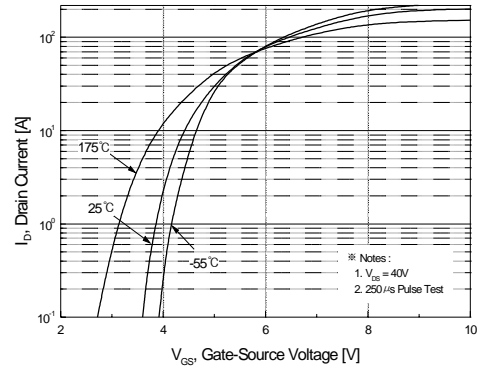
**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 0.55\text{ mH}, I_{AS} = 55\text{ A}, V_{DD} = 25\text{ V}, R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 55\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\ \mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature

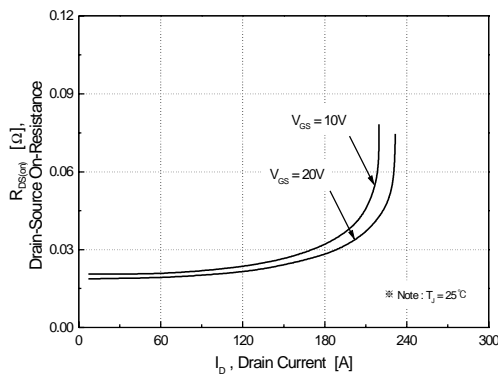
### Typical Characteristics



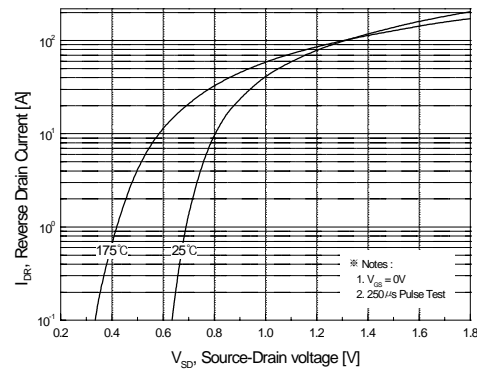
**Figure 1. On-Region Characteristics**



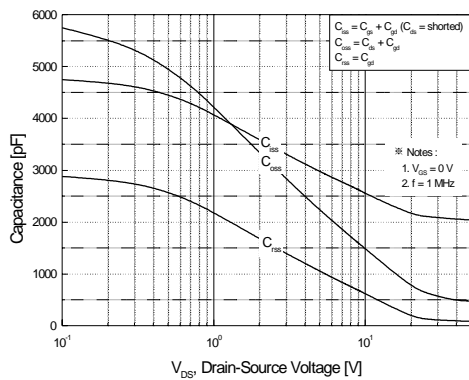
**Figure 2. Transfer Characteristics**



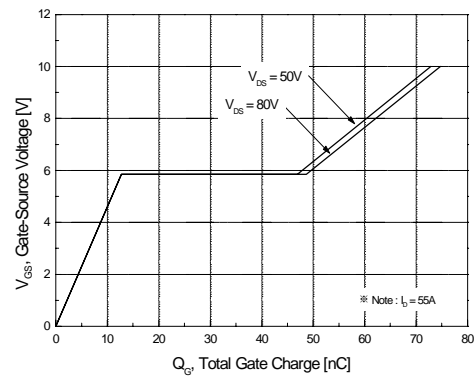
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



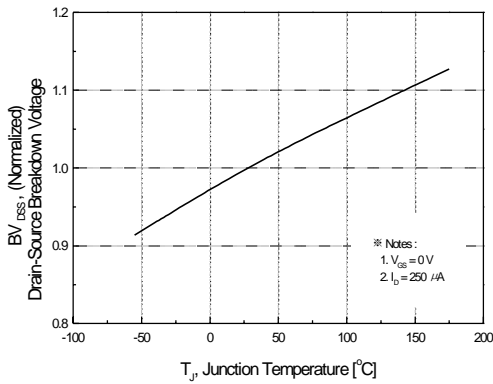
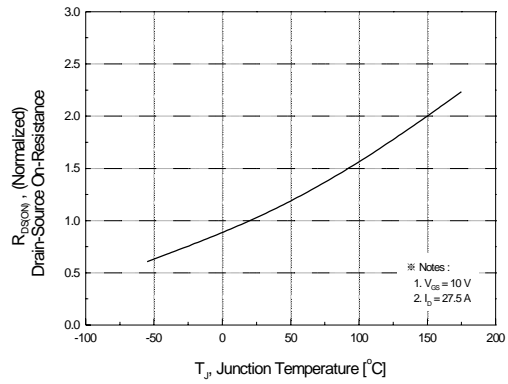
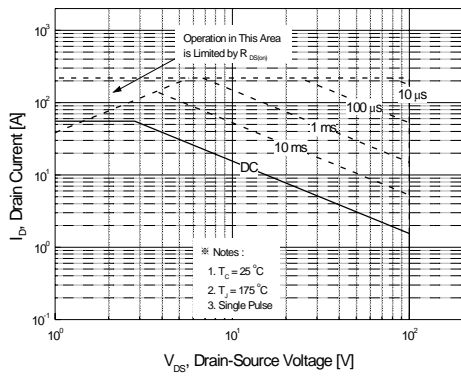
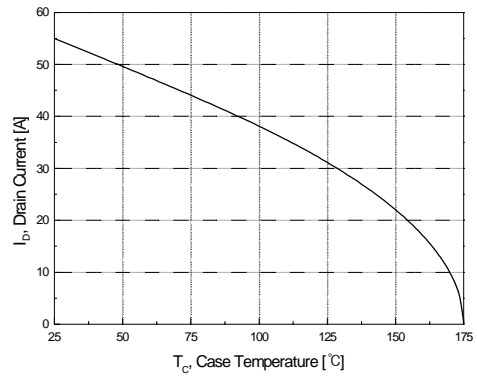
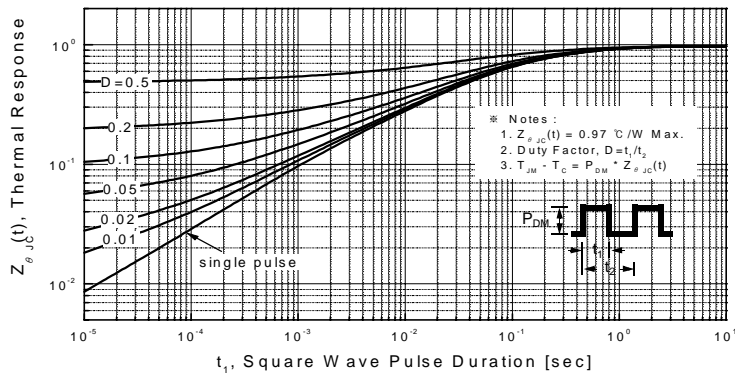
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**

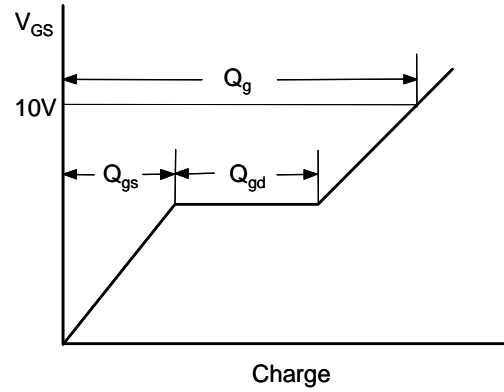
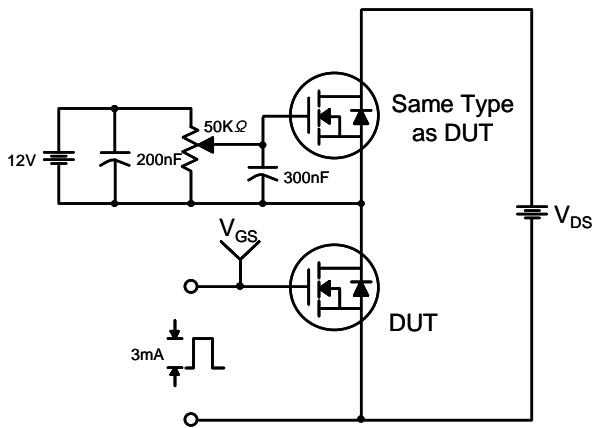
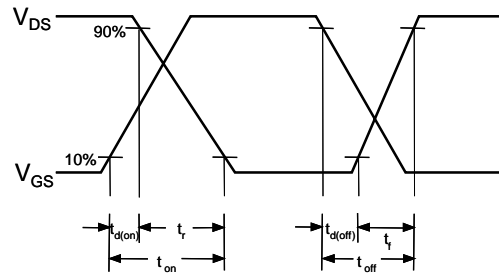
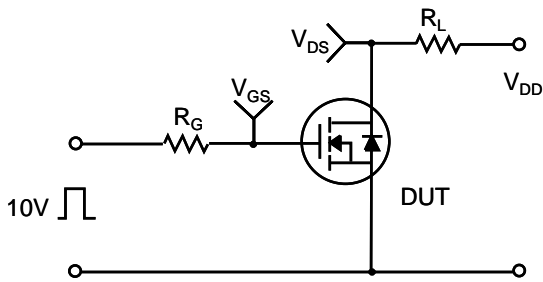
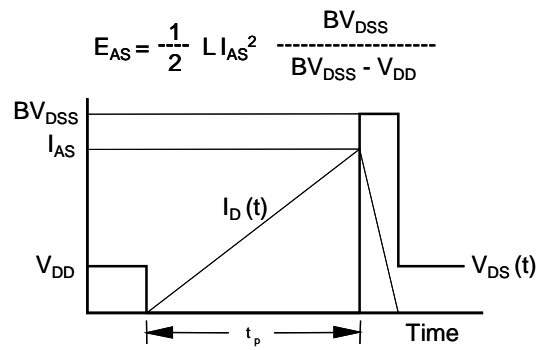
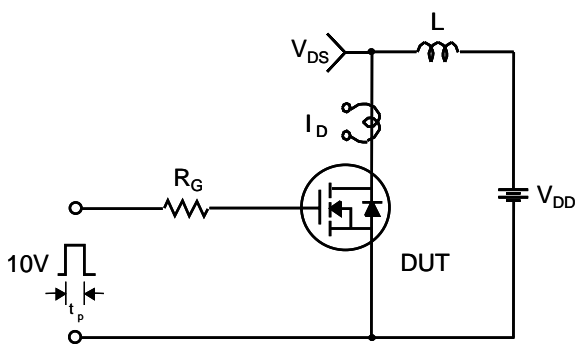


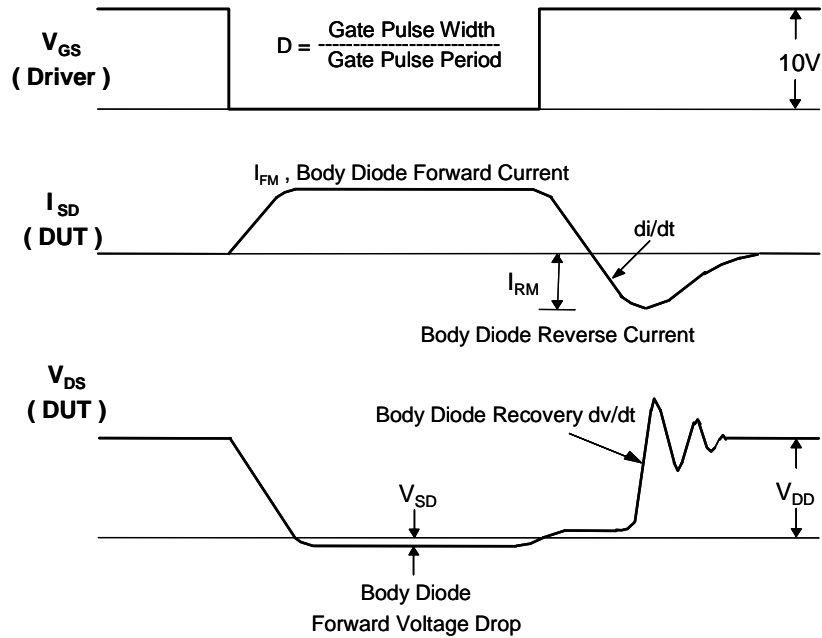
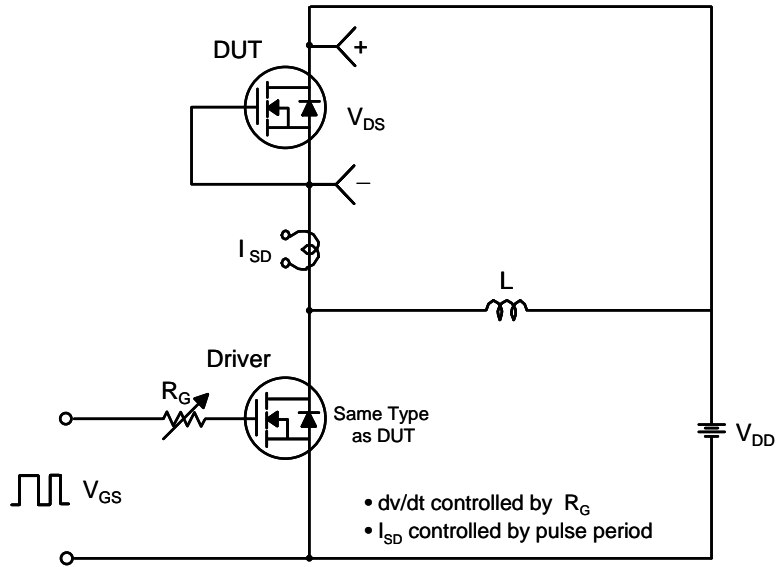
**Figure 5. Capacitance Characteristics**



**Figure 6. Gate Charge Characteristics**

**Typical Characteristics** (Continued)

**Figure 7. Breakdown Voltage Variation vs. Temperature**

**Figure 8. On-Resistance Variation vs. Temperature**

**Figure 9. Maximum Safe Operating Area**

**Figure 10. Maximum Drain Current vs. Case Temperature**

**Figure 11. Transient Thermal Response Curve**

**Gate Charge Test Circuit & Waveform**

**Resistive Switching Test Circuit & Waveforms**

**Unclamped Inductive Switching Test Circuit & Waveforms**


**Peak Diode Recovery dv/dt Test Circuit & Waveforms**


**Package Dimensions**

**TO-220**

